

# GSMDD0904

## 100V N-Channel MOSFETs

### Product Description

These N-Channel enhancement mode power field effect transistors are planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency switch mode power supply.

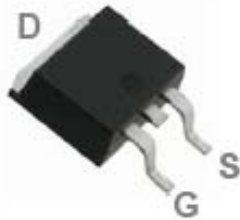
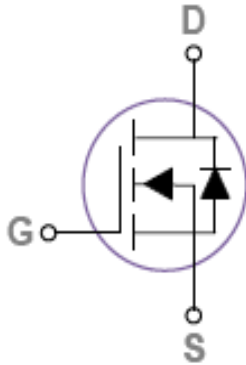
### Features

- 100V, 25A,  $R_{DS(ON)}=55m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS guaranteed
- Green Device Available
- TO-252-2L package design

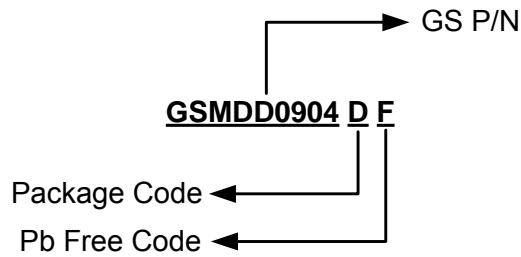
### Applications

- Networking
- Load Switch
- LED applications

### Packages & Pin Assignments

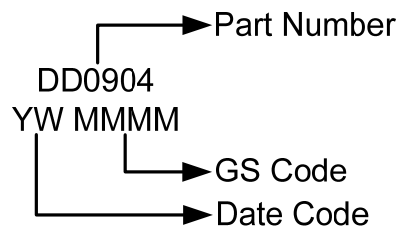
GSMDD0904DF (TO-252-2L)	
 <p>Top View</p>	
<b>Description</b>	
Gate	
Source	
Drain	

## Ordering Information



Part Number	Package	Quantity Reel
GSMDD0904DF	TO-252-2L	2500 PCS

## Marking Information



## Absolute Maximum Ratings

T<sub>A</sub>=25°C Unless otherwise noted

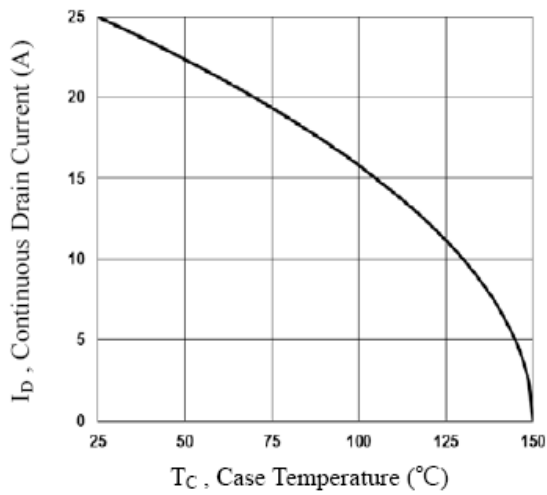
Symbol	Parameter	Typical	Unit
V <sub>DS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> =25°C	25
		T <sub>A</sub> =100°C	15
I <sub>DM</sub>	Pulsed Drain Current	100	A
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> =25°C)	73.5	W
	Power Dissipation (Derate above 25°C)	0.58	W/°C
T <sub>J</sub>	Operating Junction Temperature Range	-50 to +150	°C
T <sub>STG</sub>	Storage Temperature Range	-50 to +150	°C
R <sub>θJA</sub>	Thermal Resistance-Junction to Ambient	62	°C/W
R <sub>θJC</sub>	Thermal Resistance-Junction to Case	1.7	°C/W

## Electrical Characteristics

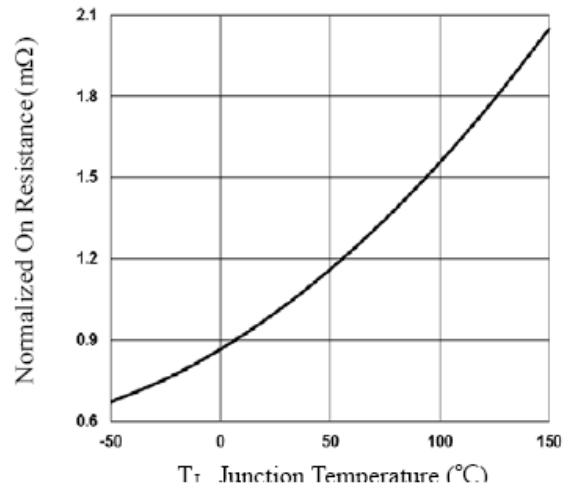
T<sub>A</sub>=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100			V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA		0.05		V/°C
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient			-5		mV/°C
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C			10	
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current			25	A
I <sub>SM</sub>	Pulsed Source Current				50	
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =10A		45	55	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		50	60	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		8.7		S
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A			1	V
<b>Dynamic</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		46	80	nC
Q <sub>gs</sub>	Gate-Source Charge			4.5	9	
Q <sub>gd</sub>	Gate-Drain Charge			12	20	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		2860	4200	pF
C <sub>oss</sub>	Output Capacitance			120	180	
C <sub>rss</sub>	Reverse Transfer Capacitance			70	105	
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =30V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω		6.8	12	ns
t <sub>r</sub>				21	40	
t <sub>d(off)</sub>	Turn-Off Time			32	60	
t <sub>f</sub>				8.2	16	
R <sub>g</sub>	Gate Resistance		V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		1.2	

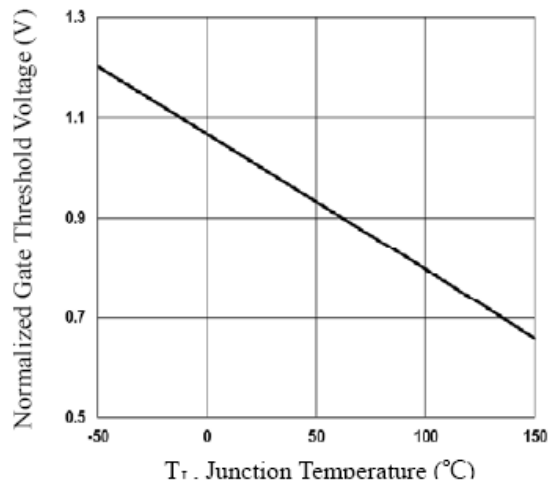
## Typical Performance Characteristics



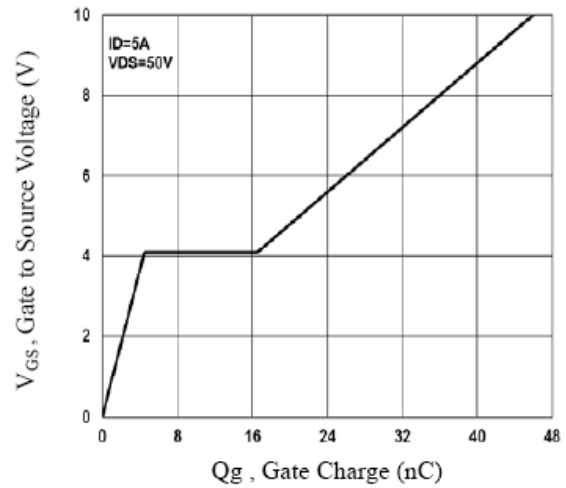
**Fig.1 Continuous Drain Current vs.  $T_c$**



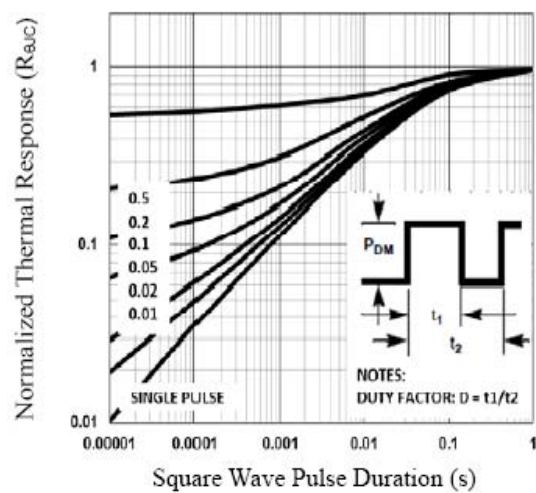
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



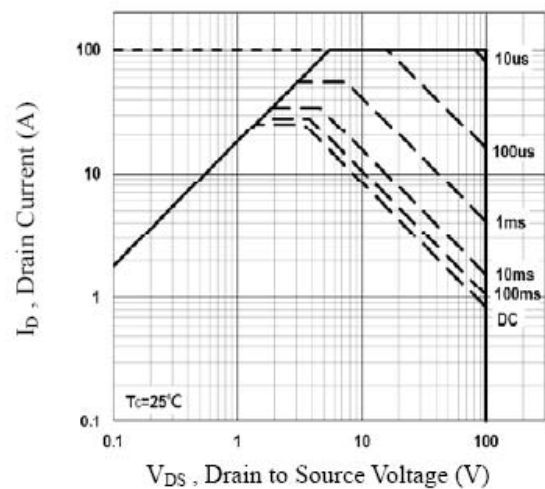
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



**Fig.4 Gate Charge Characteristics**



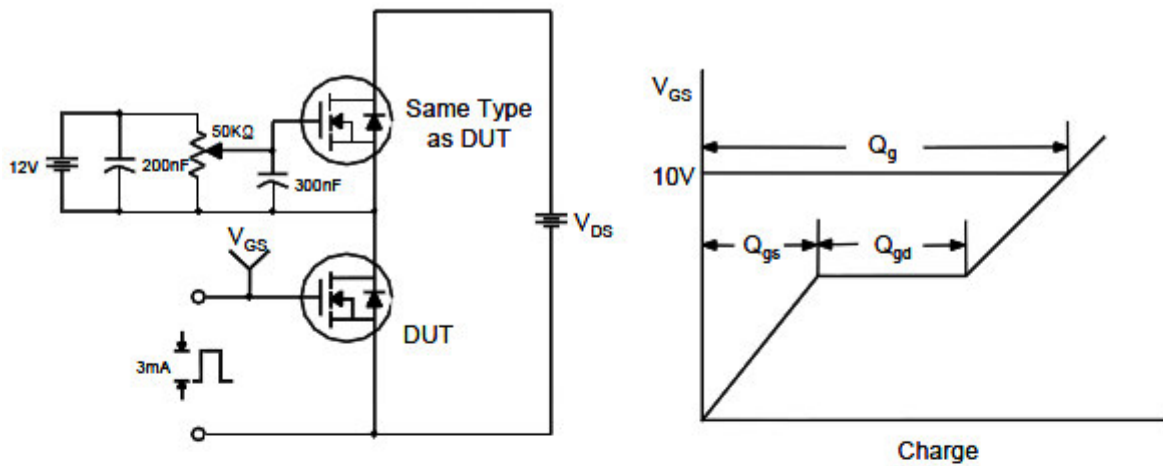
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

## Typical Performance Characteristics (Continue)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

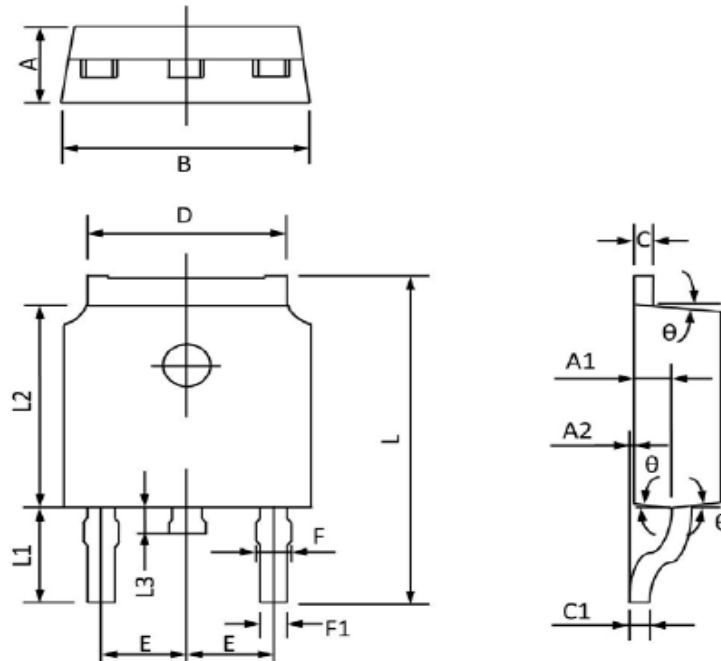


Unclamped Inductive Switching Test Circuit & Waveforms



## Package Dimension

### TO-252-2L



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.20	2.40	0.087	0.094
A1	0.91	1.11	0.036	0.044
A2	0.00	0.15	0.000	0.006
B	6.50	6.70	0.256	0.264
C	0.46	0.58	0.018	0.030
C1	0.46	0.58	0.018	0.030
D	5.10	5.46	0.201	0.215
E	2.186	2.386	0.086	0.094
F	0.74	0.94	0.029	0.037
F1	0.66	0.86	0.026	0.034
L	9.80	10.40	0.386	0.409
L1	2.9 (REF)		0.114 (REF)	
L2	6.00	6.20	0.236	0.244
L3	0.60	1.00	0.024	0.039
$\theta$	3°	9°	3°	9°

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